

Fig. 1

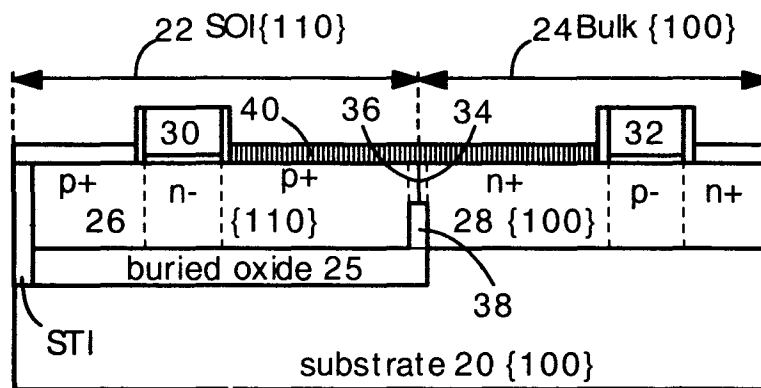


Fig. 2a

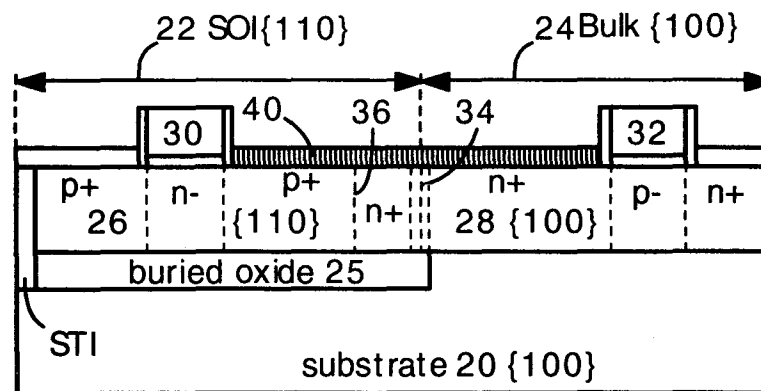


Fig. 2b

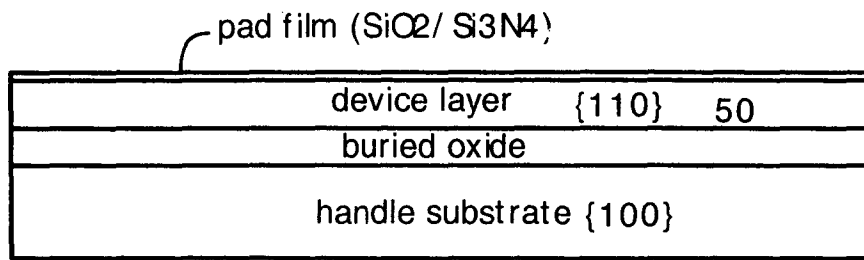


Fig. 3a SOI substrate with pad film

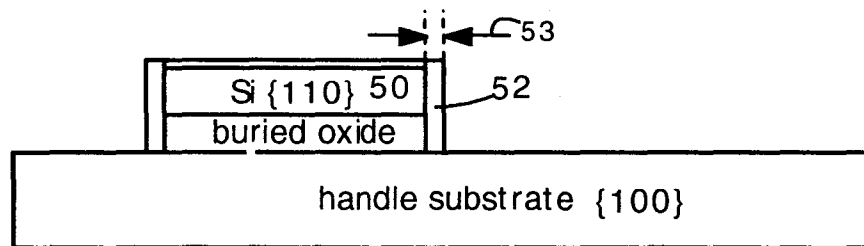


Fig. 3b Etch and form spacers

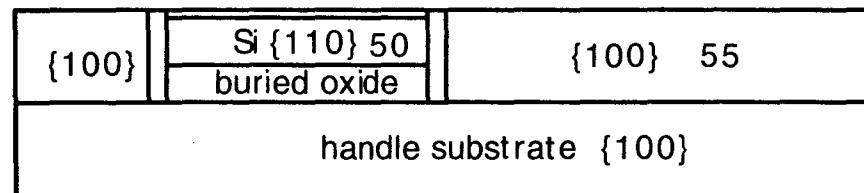


Fig. 3c Epitaxially grow substrate selectively

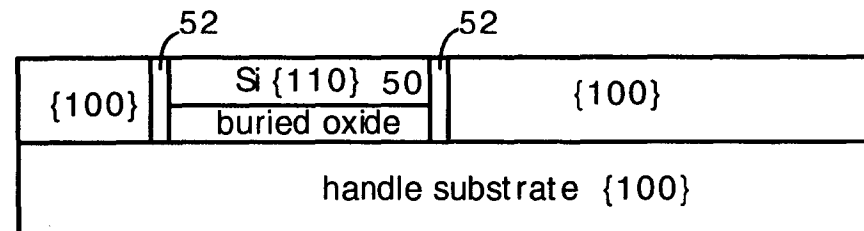


Fig. 3d Strip pad film and planarize

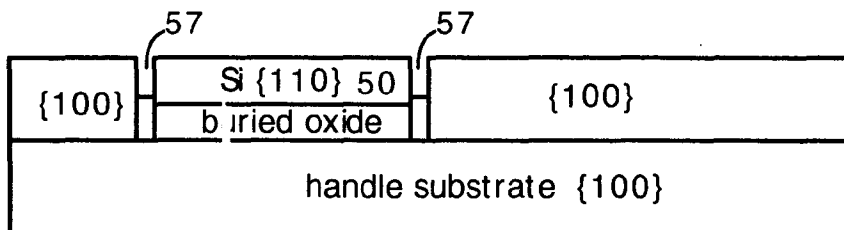


Fig. 3e Recess spacer with selective etch

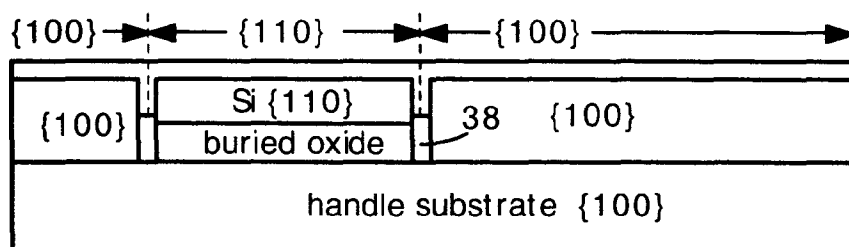


Fig. 3f Deposit epitaxial material to fill trench

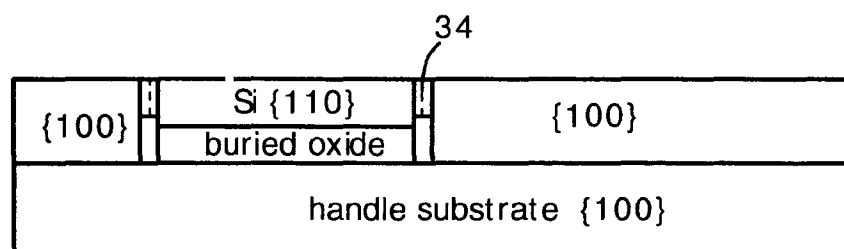


Fig. 3g Planarize

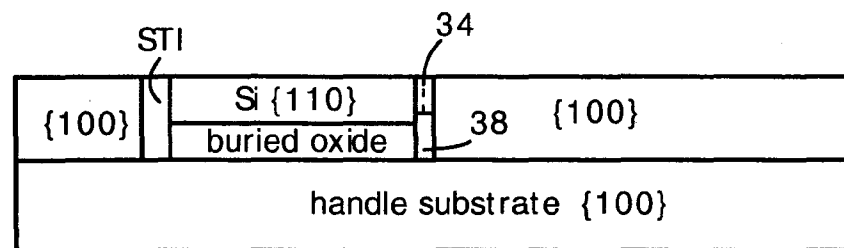


Fig. 3h Form shallow trench isolation STI

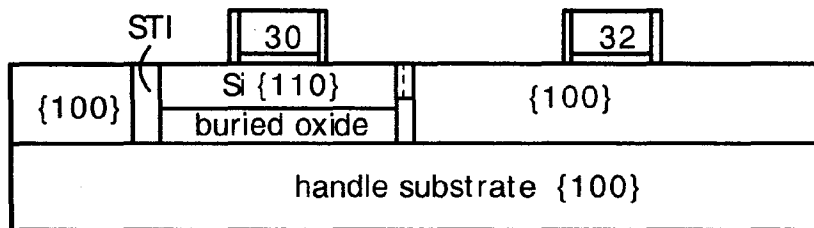


Fig. 3i Form gate electrodes and spacers

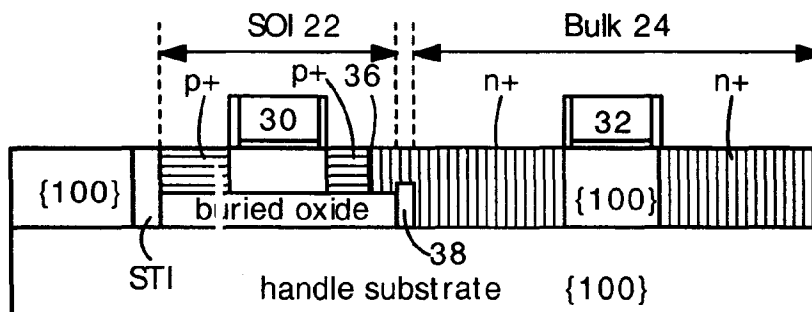


Fig. 3j Implant and form butted junction

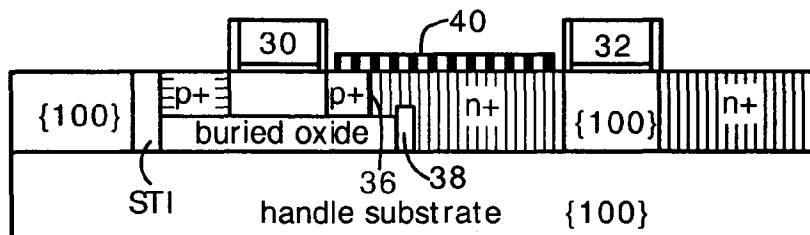


Fig. 3k Form silicide over butted junction

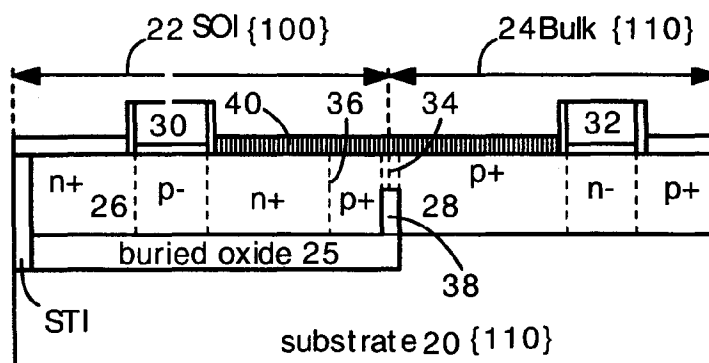


Fig. 4

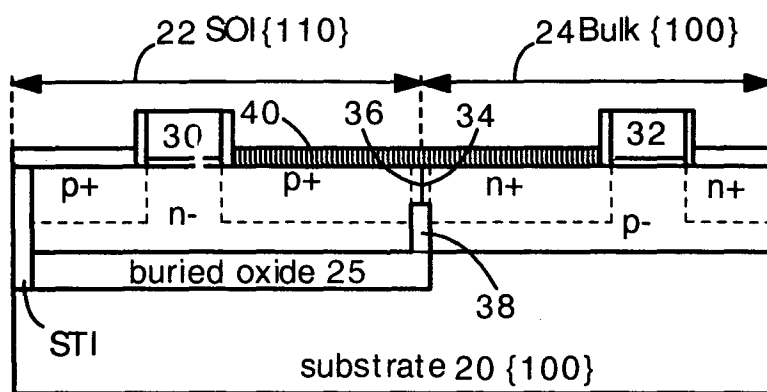


Fig. 5